优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_C = +25°C$
100V	9.5mΩ @ V_{GS} = 10V	100A

Features

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching—Ensures More Reliable and Robust End Application
- Low $R_{DS(ON)}$—Minimizes Power Losses
- Low Qg—Minimizes Switching Losses

Description and Applications

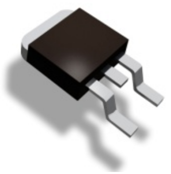
This new generation N-channel enhancement mode MOSFET is designed to minimize $R_{DS(ON)}$ yet maintain superior switching performance. This device is ideal for high-efficiency power management applications.

- Synchronous Rectification
- Inverter
- DC-DC Converters

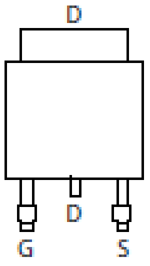
Mechanical Data

- Case: TO263AB (D2PAK)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 1.7 grams (Approximate)

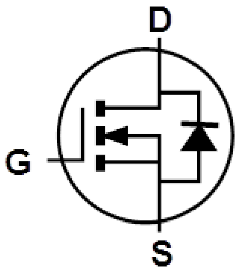
TO263AB (D2PAK)



Top View



Pin Out Top View



Internal Schematic

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	T_C = +25°C T_C = +100°C	I_D	100 71	A
Maximum Continuous Body Diode Forward Current	T_C = +25°C	I_S	110	A
Pulsed Drain Current (10µs Pulse, T_C=+25°C, Package Limited)		I_{DM}	400	A
Pulsed Body Diode Forward Current (10µs Pulse, T_C=+25°C, Package Limited)		I_{SM}	400	A
Avalanche Current, L=0.3mH (Note 7)		I_{AS}	35	A
Avalanche Energy, L=0.3mH (Note 7)		E_{AS}	187	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	3.9	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	32	°C/W
Total Power Dissipation	T_C = +25°C	P_D	125	W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	1.0	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 80V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.4	2.0	3.5	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	8.7	9.5	mΩ	V_{GS} = 10V, I_D = 13A
		—	13.2	17		V_{GS} = 4.5V, I_D = 13A
Diode Forward Voltage	V_{SD}	—	0.8	1.3	V	V_{GS} = 0V, I_S = 13A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	2592	—	pF	V_{DS} = 50V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	792	—		
Reverse Transfer Capacitance	C_{rss}	—	45	—		
Gate Resistance	R_g	—	2	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	53.7	—	nC	V_{DD} = 50V, I_D = 13A, V_{GS} = 10V
Gate-Source Charge	Q_{gs}	—	10.6	—		
Gate-Drain Charge	Q_{gd}	—	8.2	—		
Turn-On Delay Time	$t_{D(ON)}$	—	11.6	—	ns	V_{DD} = 50V, V_{GS} = 10V, I_D = 13A, R_g = 6Ω
Turn-On Rise Time	t_R	—	14.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	42.9	—		
Turn-Off Fall Time	t_F	—	22	—		
Reverse Recovery Time	t_{RR}	—	49.8	—	ns	I_F = 13A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	85.1	—	nC	

Notes:
5. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

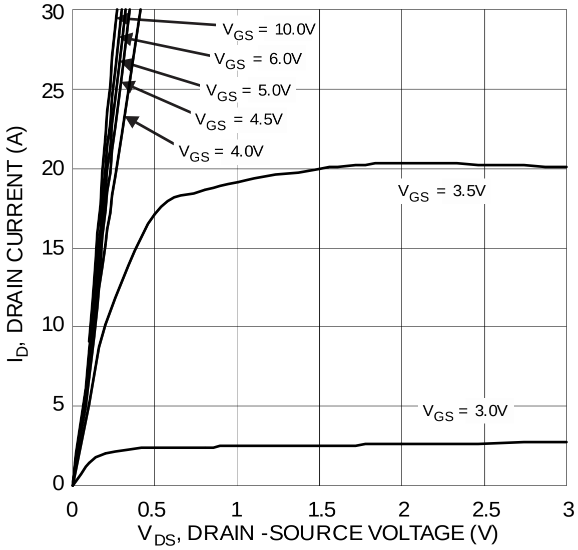


Figure 1 Typical Output Characteristics

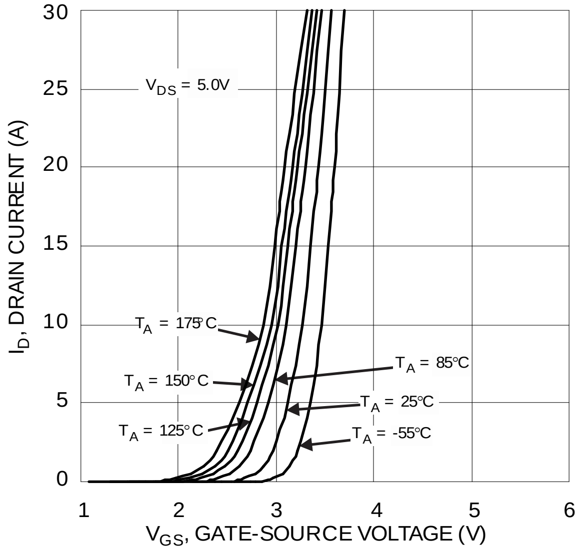


Figure 2 Typical Transfer Characteristics

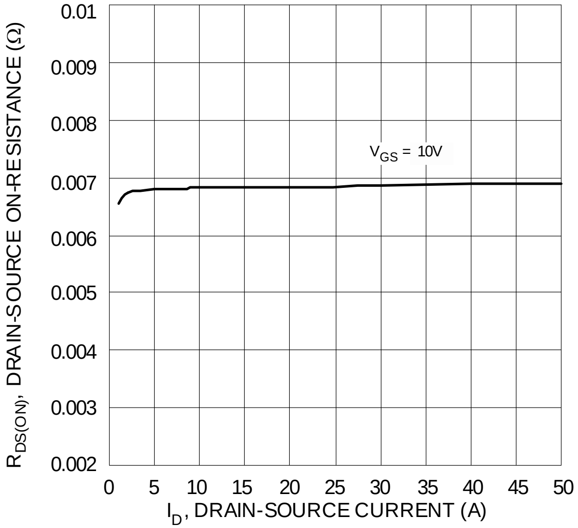


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

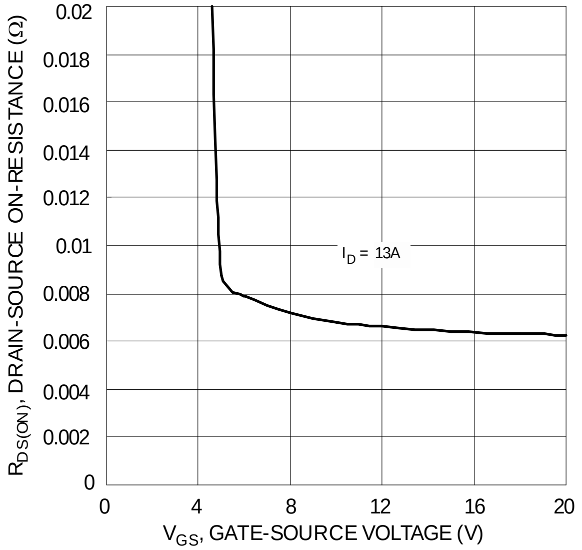


Figure 4 Typical Transfer Characteristics

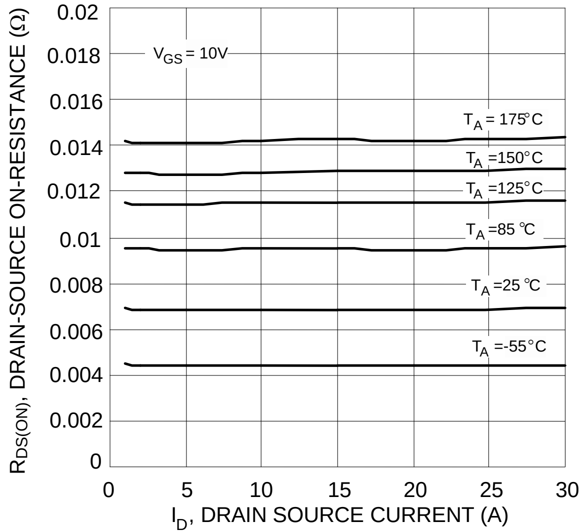


Figure 5 Typical On-Resistance vs.
Drain Current and Junction Temperature

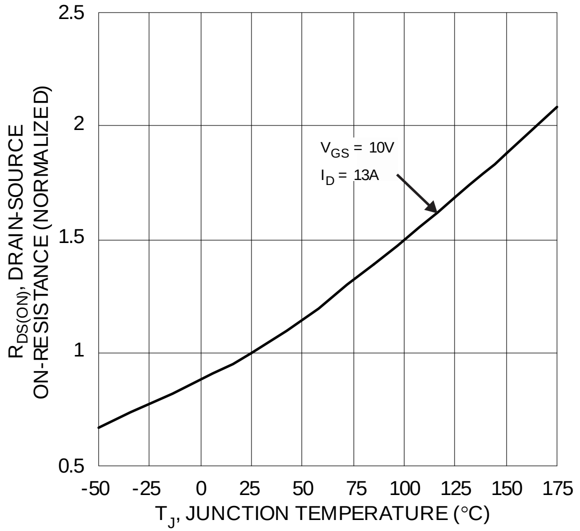


Figure 6 On-Resistance Variation with
Junction Temperature

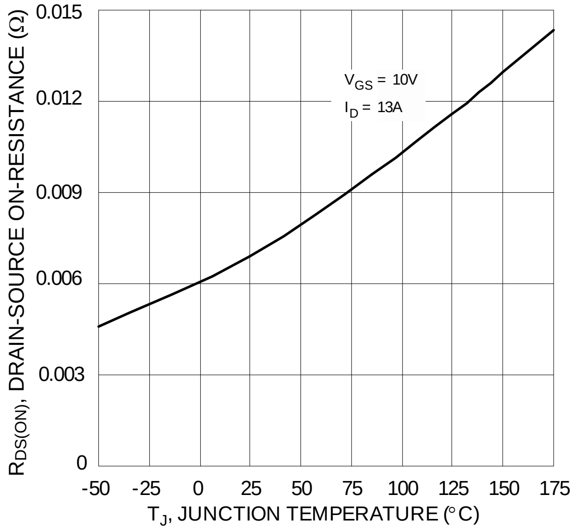


Figure 7 On-Resistance Variation with Junction Temperature

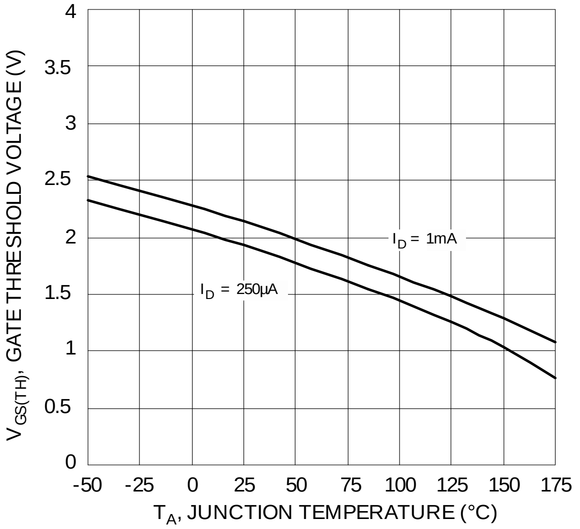


Figure 8 Gate Threshold Variation vs. Junction Temperature

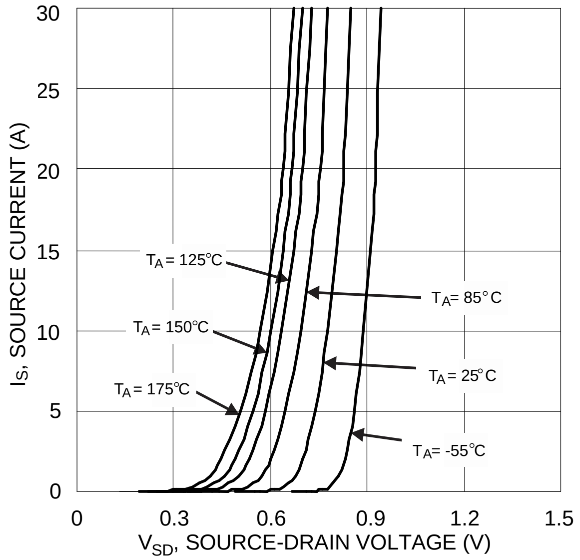


Figure 9 Diode Forward Voltage vs. Current

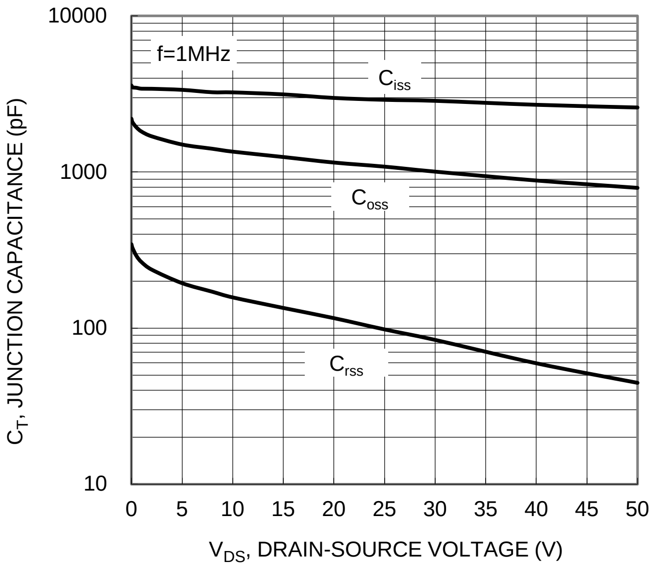


Figure 10. Typical Junction Capacitance

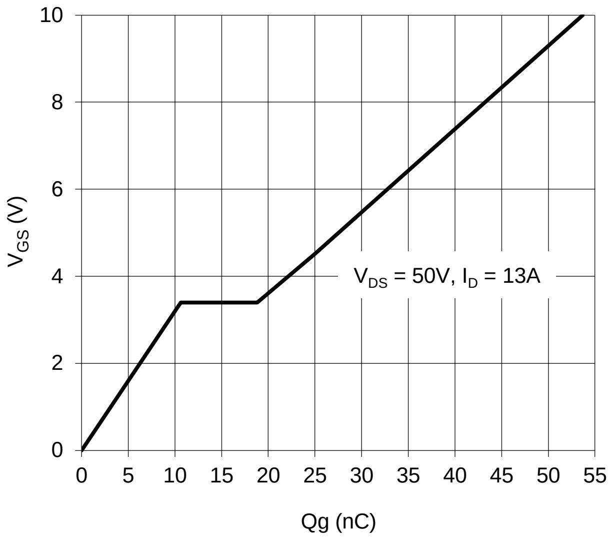


Figure 11. Gate Charge

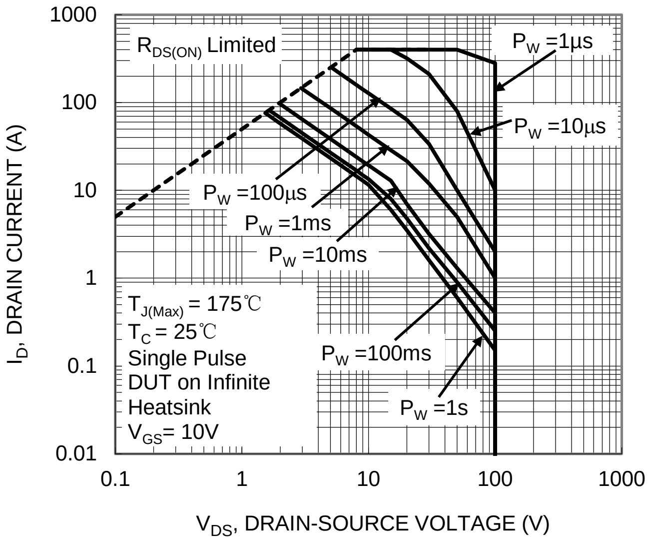


Figure 12. SOA, Safe Operation Area

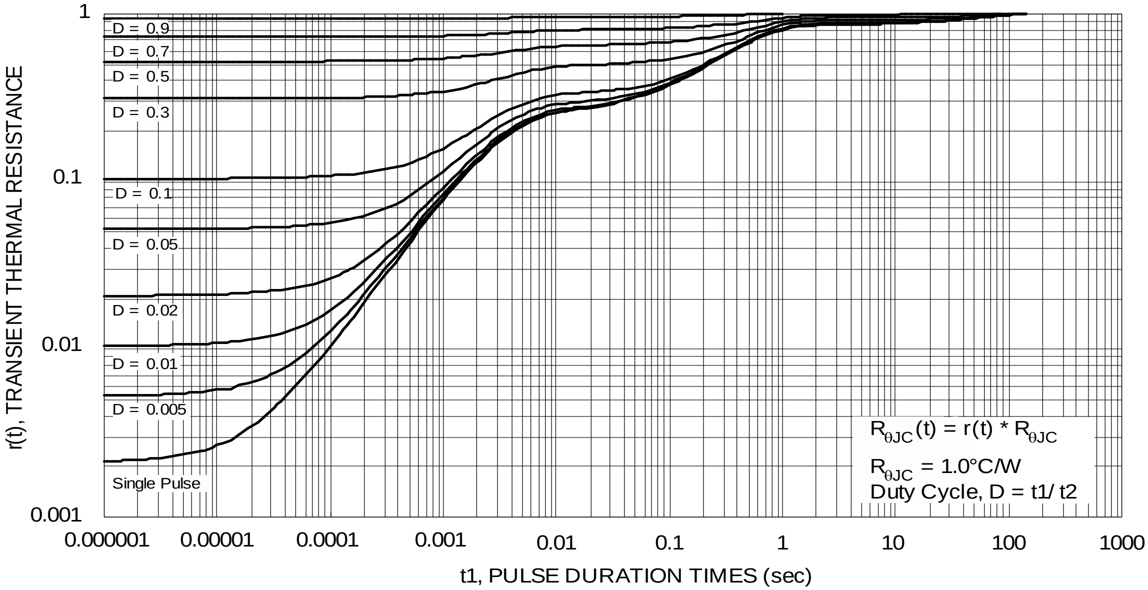
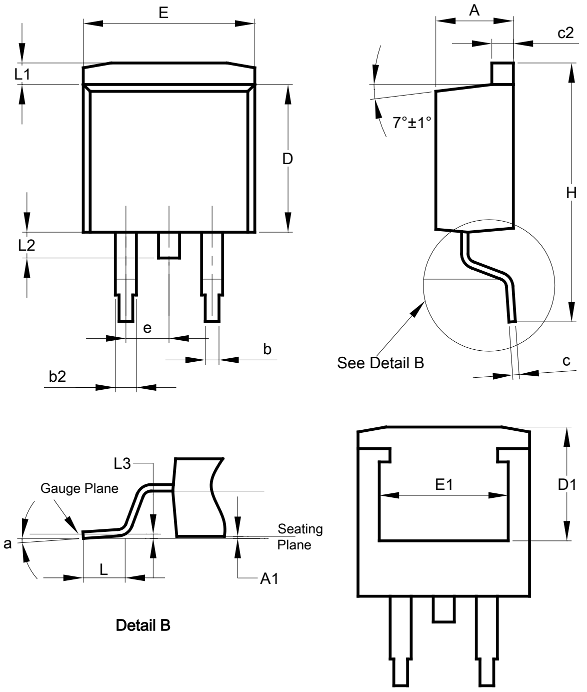


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

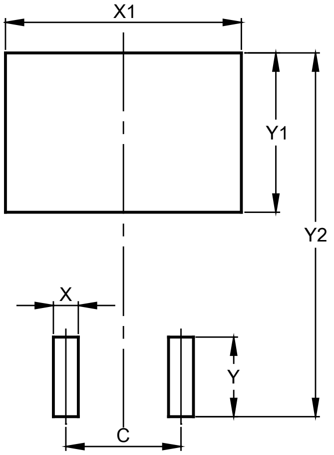
TO263AB (D2PAK)



TO263AB (D2PAK)			
Dim	**Min**	**Max**	**Typ**
A	4.07	4.82	-
A1	0.00	0.25	-
b	0.51	0.99	-
b2	1.15	1.77	-
c	0.356	0.73	-
c2	1.143	1.65	-
D	8.39	9.65	-
D1	6.55	6.95	-
e	2.54 TYP		
E	9.66	10.66	-
E1	6.23	8.23	-
H	14.61	15.87	-
L	1.78	2.79	-
L1	-	1.67	-
L2	-	1.77	-
L3	-	-	0.254
a	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

TO263AB (D2PAK)



Dimensions	Value (in mm)
C	5.08
X	1.10
X1	10.41
Y	3.50
Y1	7.01
Y2	15.99